Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 https://www.sciencedirect.com/science/article/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill https://www.sciencedirect.com/science/article/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, C. A. The 9th International Conference on Global Research and Education : August 9-12, 2010, Riga : digest 2010 / p. 231-233 https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564

Stress relaxation mechanism by strain in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262